

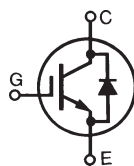
**XPT™ 600V IGBT**  
**GenX3™ w/Diode**
**IXXN200N60B3H1**

$$V_{CES} = 600V$$

$$I_{C110} = 98A$$

$$V_{CE(sat)} \leq 1.7V$$

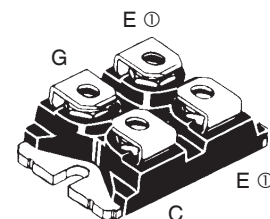
$$t_{fi(typ)} = 110ns$$


 Extreme Light Punch Through  
 IGBT for 10-30kHz Switching

SOT-227B, miniBLOC

E153432

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ (Chip Capability)	200	A
$I_{C110}$	$T_C = 110^\circ C$	98	A
$I_{F110}$	$T_C = 110^\circ C$	30	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	1000	A
$I_A$	$T_C = 25^\circ C$	100	A
$E_{AS}$	$T_C = 25^\circ C$	1	J
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 400$ @ $V_{CE} \leq V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 360V$ , $T_J = 150^\circ C$ $R_G = 10\Omega$ , Non Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	780	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$V_{ISOL}$	50/60Hz $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
$M_d$	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
<b>Weight</b>		30	g



G = Gate, C = Collector, E = Emitter

 ① either emitter terminal can be used as  
 Main or Kelvin Emitter

**Features**

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- miniBLOC, with Aluminium Nitride Isolation
- Optimized for Low Conduction and Switching Losses
- Isolated Mounting Surface
- Anti-Parallel Ultra Fast Diode
- 2500V~ Electrical Isolation
- Optimized for 10-30kHz Switching
- Avalanche Rated
- Short Circuit Capability
- Very High Current Capability
- Square RBSOA

**Advantages**

- High Power Density
- Low Gate Drive Requirement

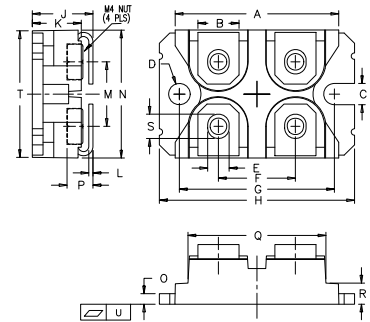
**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.5		6.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ Note 2, $T_J = 150^\circ C$			50 $\mu A$ 3 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 200$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		1.40 1.58	V V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	27	45	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9970	pF
$C_{oes}$			570	pF
$C_{res}$			183	pF
$Q_{g(on)}$	$I_C = 200\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		315	nC
$Q_{ge}$			98	nC
$Q_{gc}$			130	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 360\text{V}, R_G = 1\Omega$ Note 3		48	ns
$t_{ri}$			100	ns
$E_{on}$			2.85	mJ
$t_{d(off)}$			160	ns
$t_{fi}$			110	ns
$E_{off}$		2.90	4.40	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 360\text{V}, R_G = 1\Omega$ Note 3		46	ns
$t_{ri}$			94	ns
$E_{on}$			4.40	mJ
$t_{d(off)}$			180	ns
$t_{fi}$			215	ns
$E_{off}$		3.45	mJ	
$R_{thJC}$			0.16	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### SOT-227B miniBLOC (IXXN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

### Reverse Diode (FRED)

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 100\text{A}, V_{GE} = 0\text{V}$ , Note 1			2.5 V
	$T_J = 150^\circ\text{C}$		2.3	V
$I_{RM}$	$I_F = 100\text{A}, V_{GE} = 0\text{V},$ $-di_F/dt = 1500\text{A}/\mu\text{s}, V_R = 300\text{V}$		95	A
$t_{rr}$			100	ns
$R_{thJC}$				0.70 $^\circ\text{C/W}$

### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Part must be heatsunk for high-temp  $I_{ces}$  measurement.
3. Switching times & energy losses may increase for higher  $V_{CE(Clamp)}$ ,  $T_J$  or  $R_G$ .

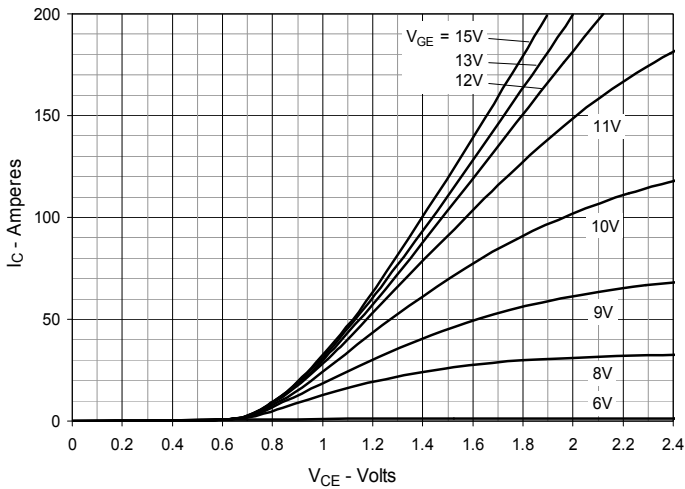
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

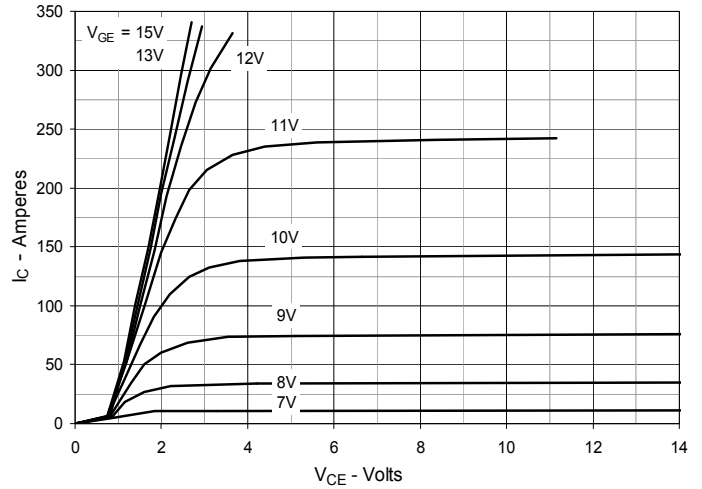
### IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

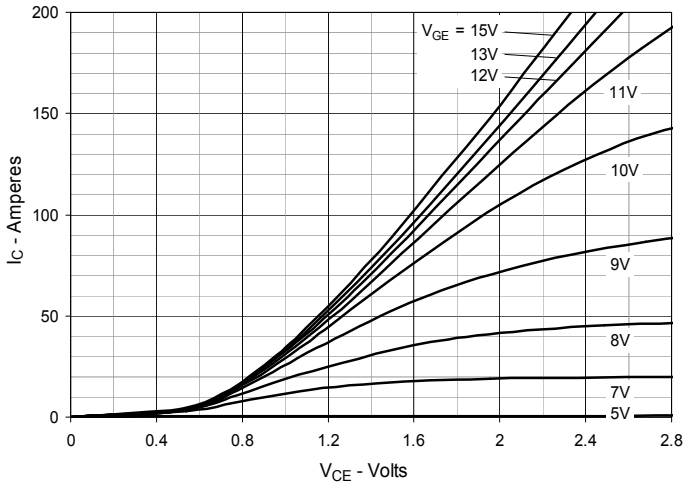
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



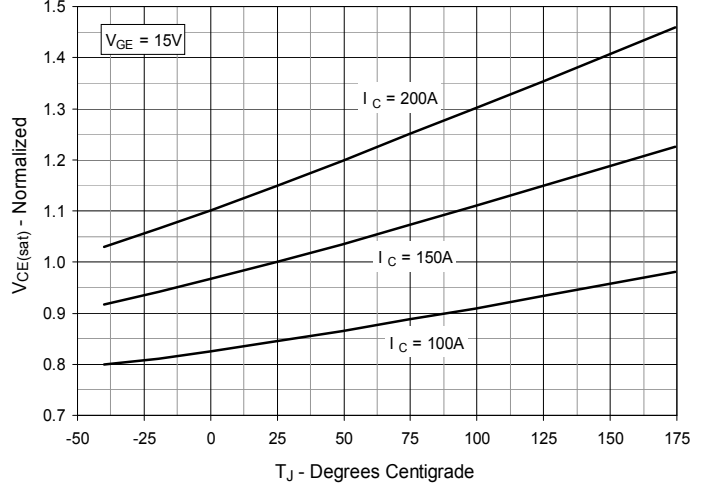
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



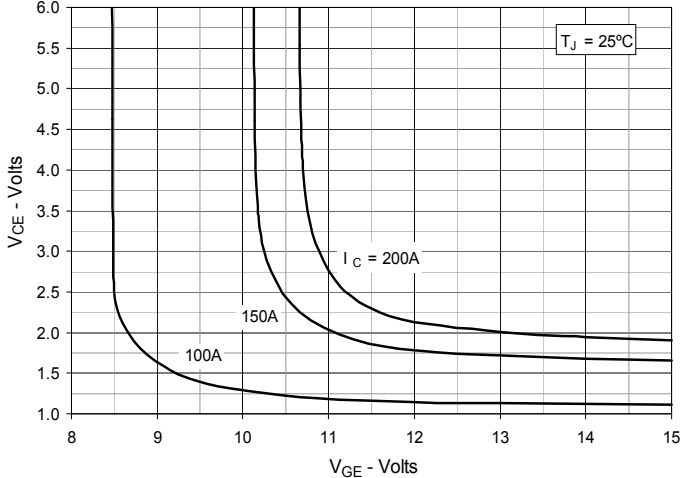
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



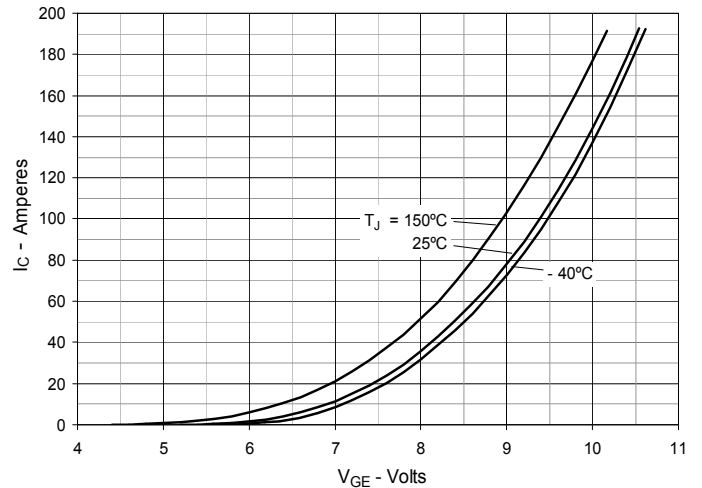
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



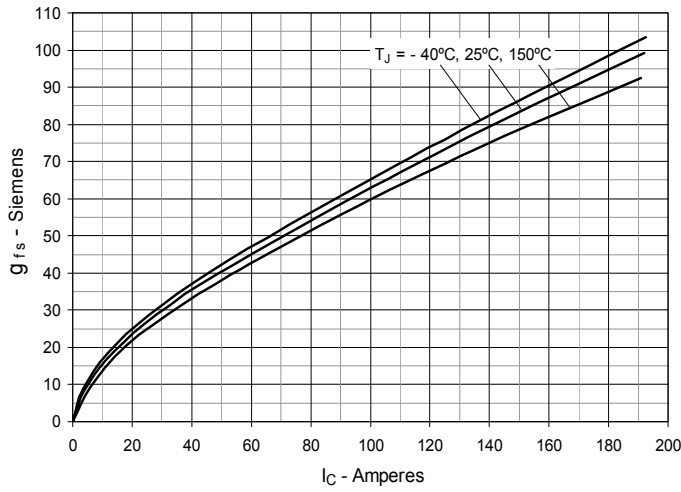
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



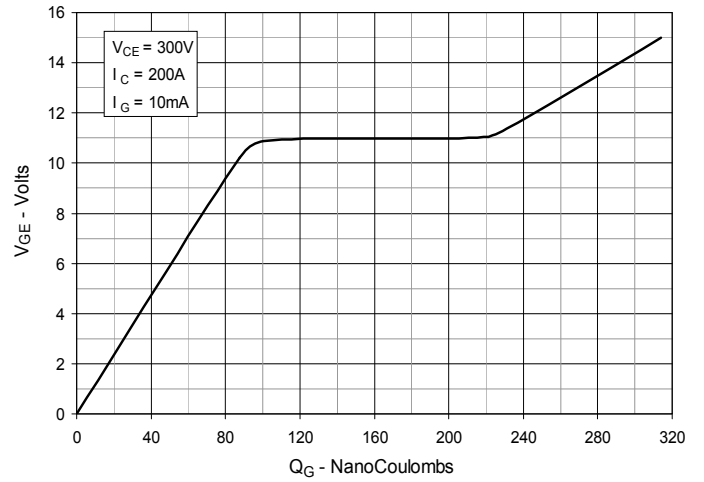
**Fig. 6. Input Admittance**



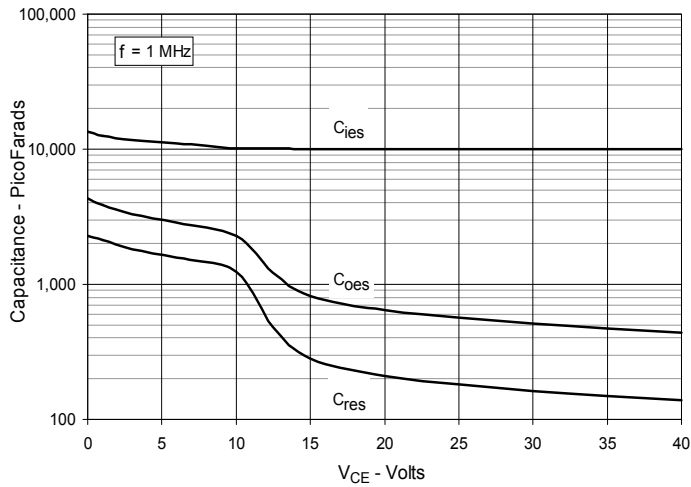
**Fig. 7. Transconductance**



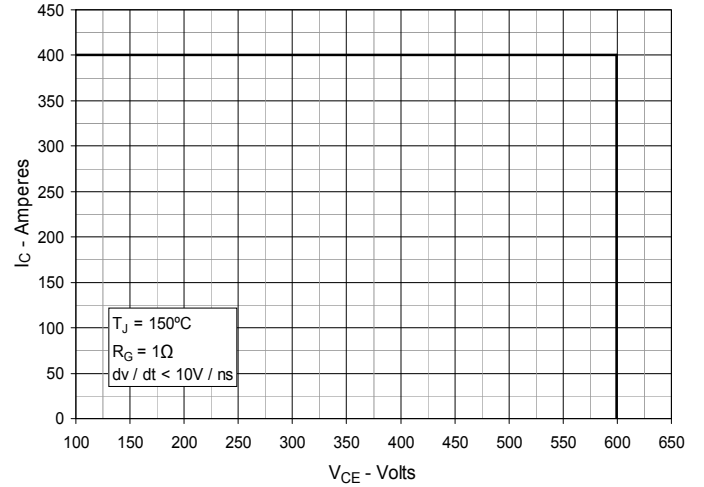
**Fig. 8. Gate Charge**



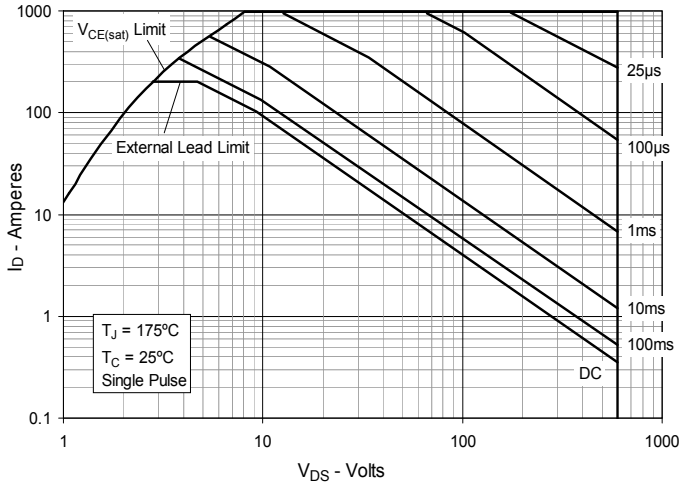
**Fig. 9. Capacitance**



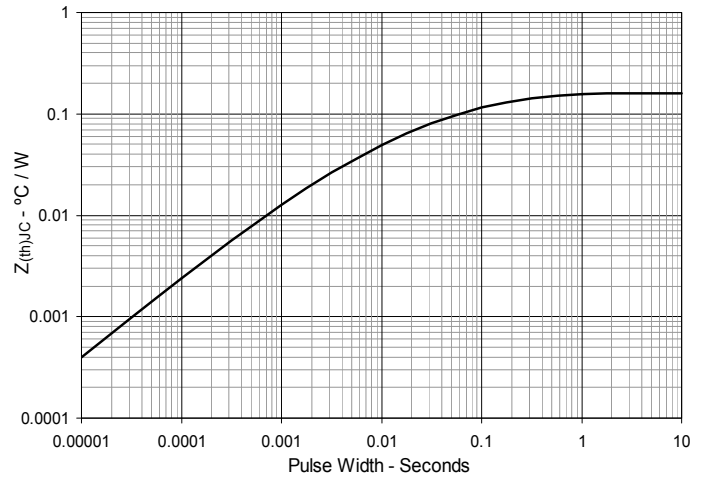
**Fig. 10. Reverse-Bias Safe Operating Area**



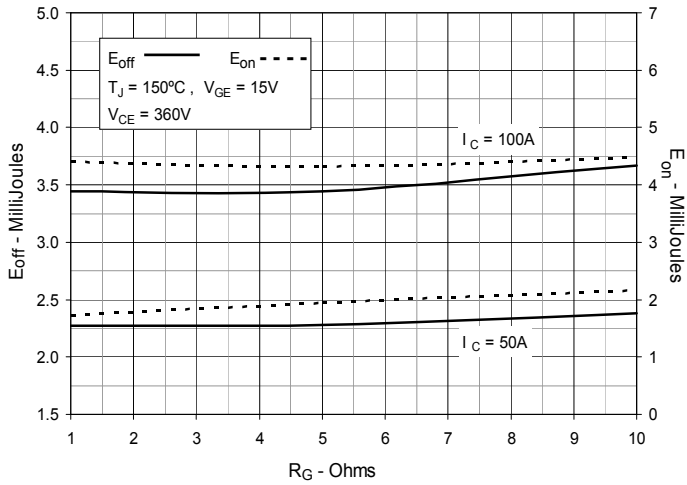
**Fig. 11. Forward-Bias Safe Operating Area**



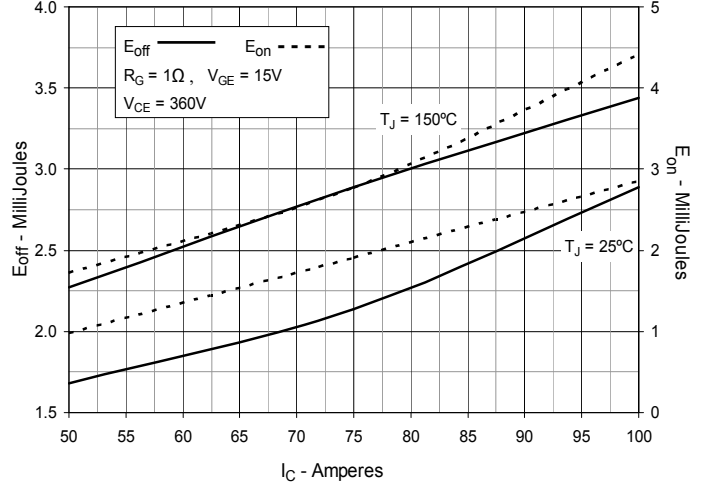
**Fig. 12. Maximum Transient Thermal Impedance**



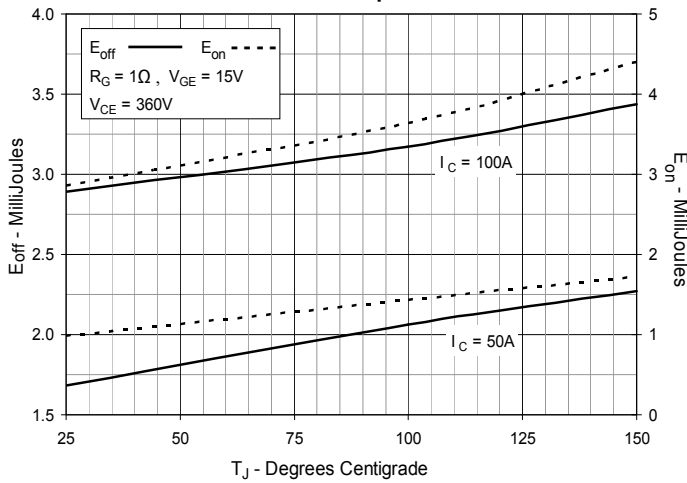
**Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance**



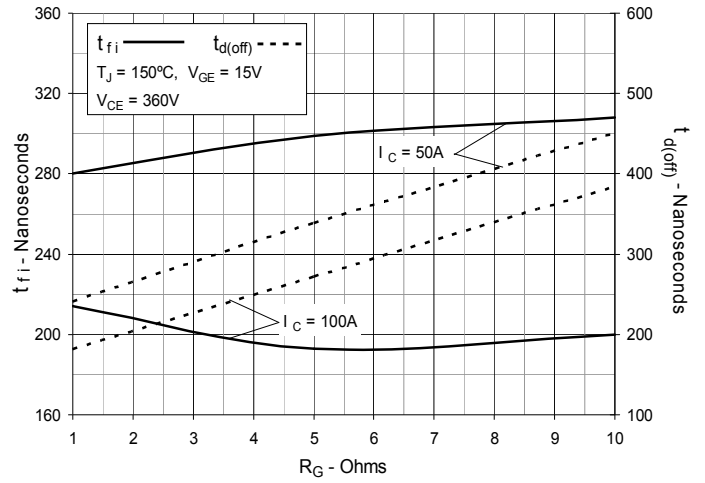
**Fig. 14. Inductive Switching Energy Loss vs. Collector Current**



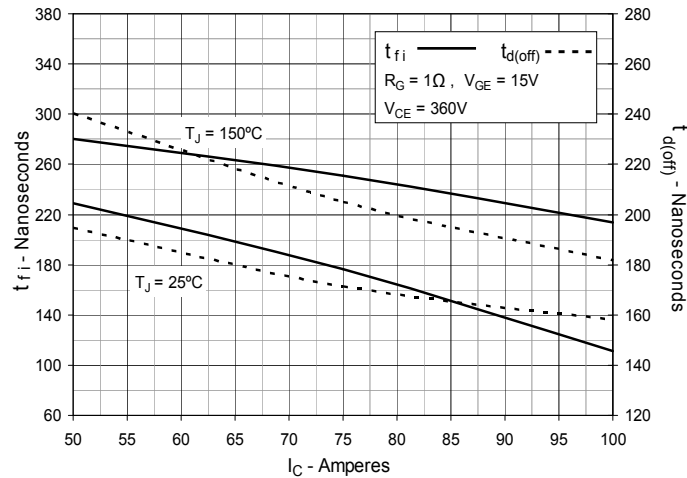
**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**



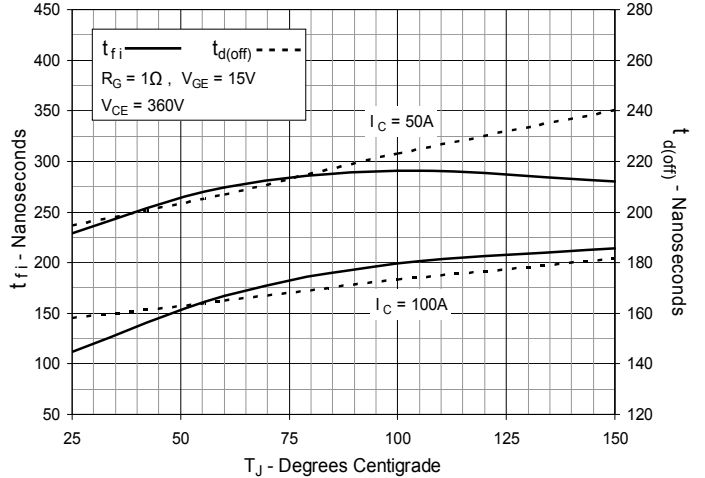
**Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance**

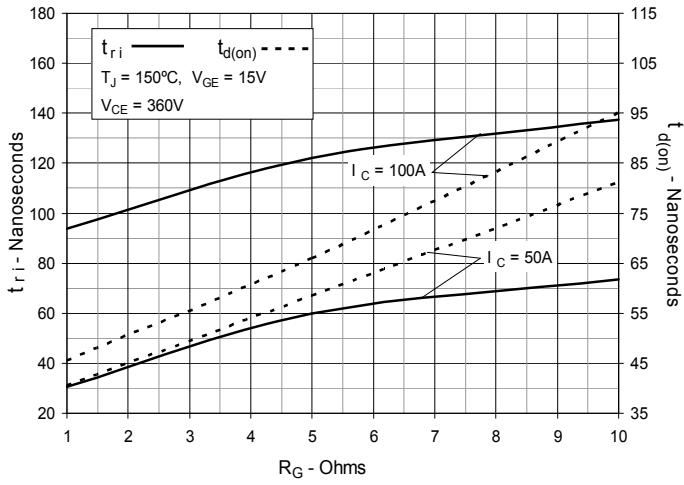
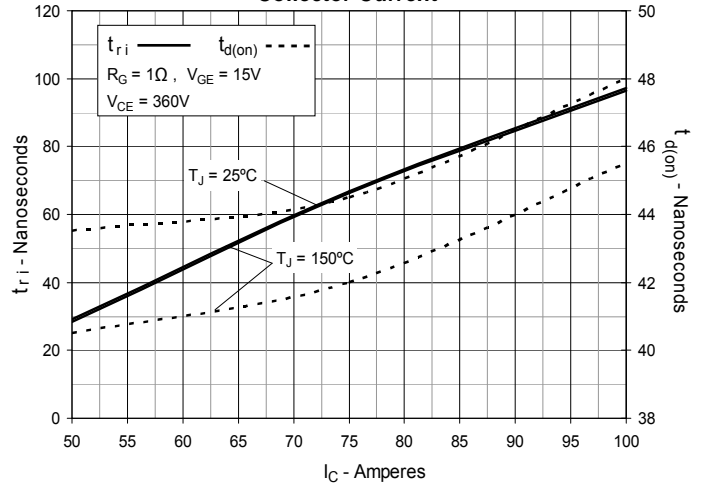
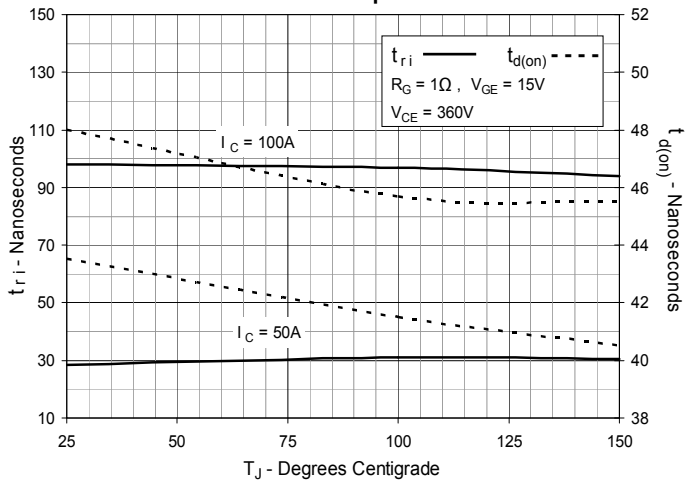


**Fig. 17. Inductive Turn-off Switching Times vs. Collector Current**

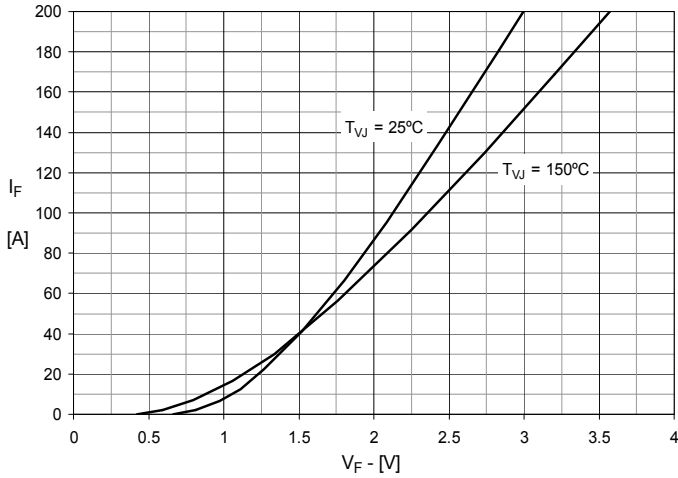


**Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature**

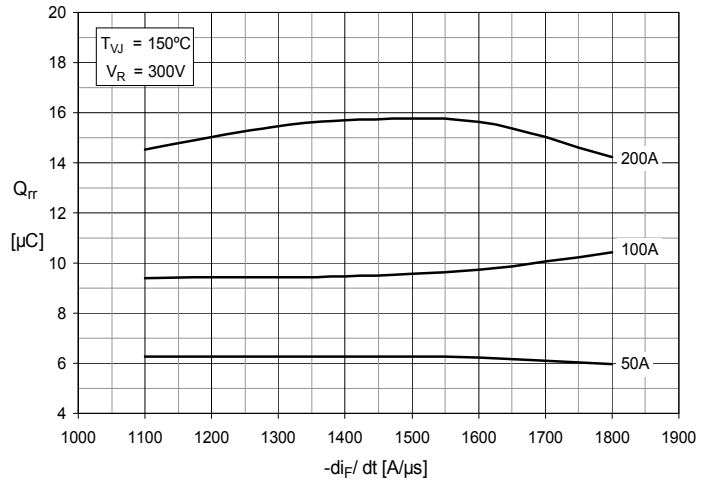


**Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 20. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature**


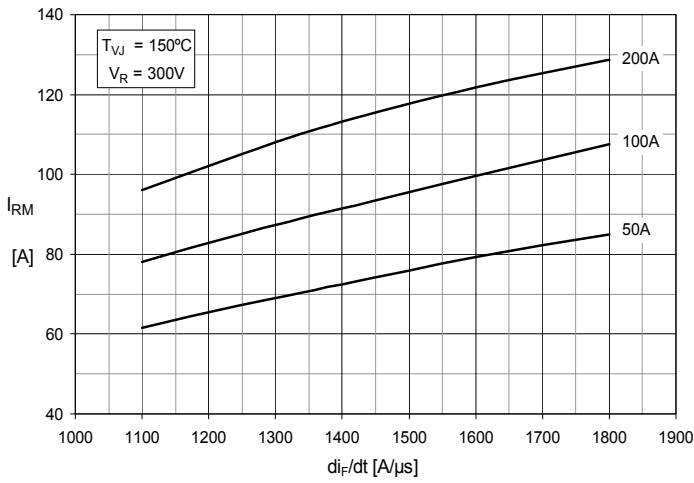
**Fig. 22. Typ. Forward characteristics**



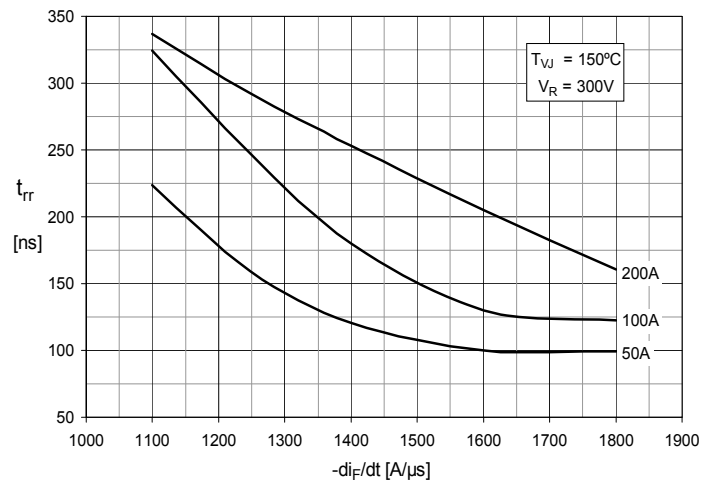
**Fig. 23. Typ. Reverse Recovery Charge  $Q_{rr}$  vs.  $-di_F/dt$**



**Fig. 24. Typ. Peak Reverse Current  $I_{RM}$  vs.  $-di_F/dt$**



**Fig. 25. Typ. Recovery Time  $t_{rr}$  vs.  $-di_F/dt$**



**Fig. 26. Typ. Recovery Energy  $E_{rec}$  vs.  $-di_F/dt$**

